

# Towards Cell-Aware Test For Small Delay Faults

## Study Project

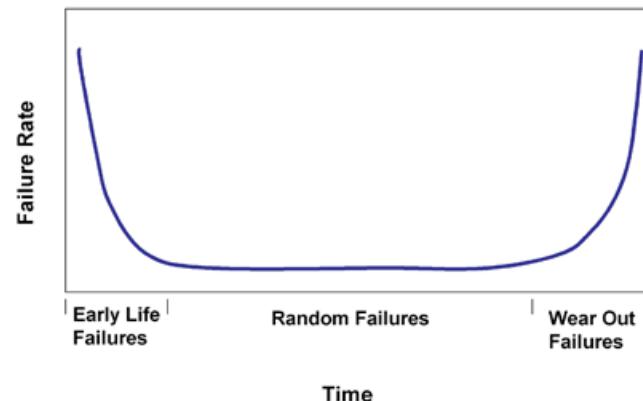
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Professor: Dr. Hans-Joachim Wunderlich

June 09, 2021

- **What is the problem ?**
  - Manufacturing test - nominal frequency set
  - Small delays - escapes this test
- **Result of the problem**
  - Early life failure of the device



- **Solution**
  - Inserting defects with high probability, resulting in small delay
  - Efficient & realistic defect model generation, helping in analysis of small delay

# Outline

- **Introduction**
- **Preliminaries**
- **Tool Overview & Results**
- **Conclusion**

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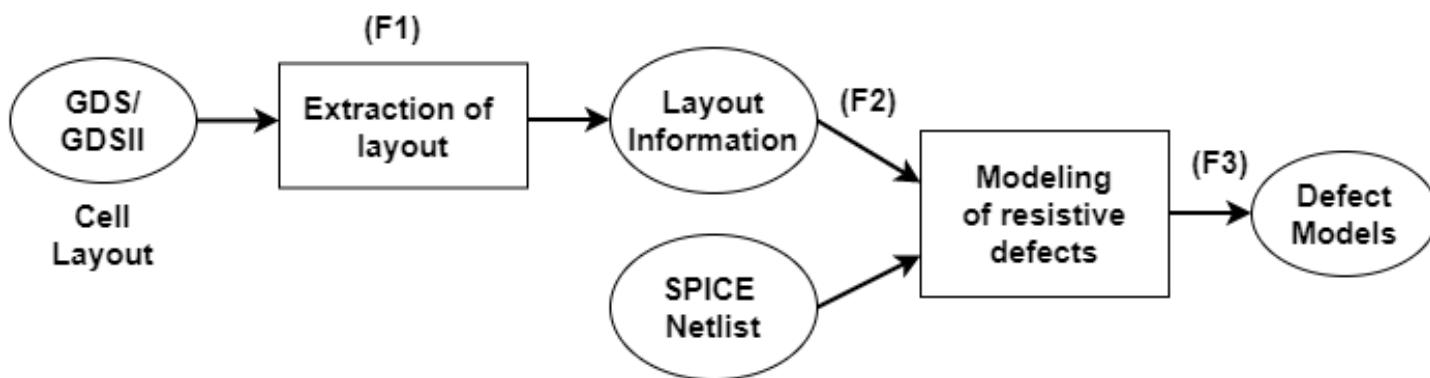
# Motivation

- Transistors Count - doubles every two years
  - Thousands in 1970's to billions at present
- Increase in transistors → increase in defects
  - Solution: demand for higher quality tests
- Technology scaling down from 10µm (1971) to 5 nm (2020)
  - One of the results: a lot of timing-related defects
- Small delay defects - extra small delay in circuit
- Increases at field level → resulting in early life failure of the device

# Cell-Aware Test

- Timing-related defects found in standard cell library
  - Cell internal defects are the most predominant
- Cell-Aware Test (CAT)
  - Testing the cell using layout information
- New era in defect modeling and defect circuit analysis

# Focus of Study Project



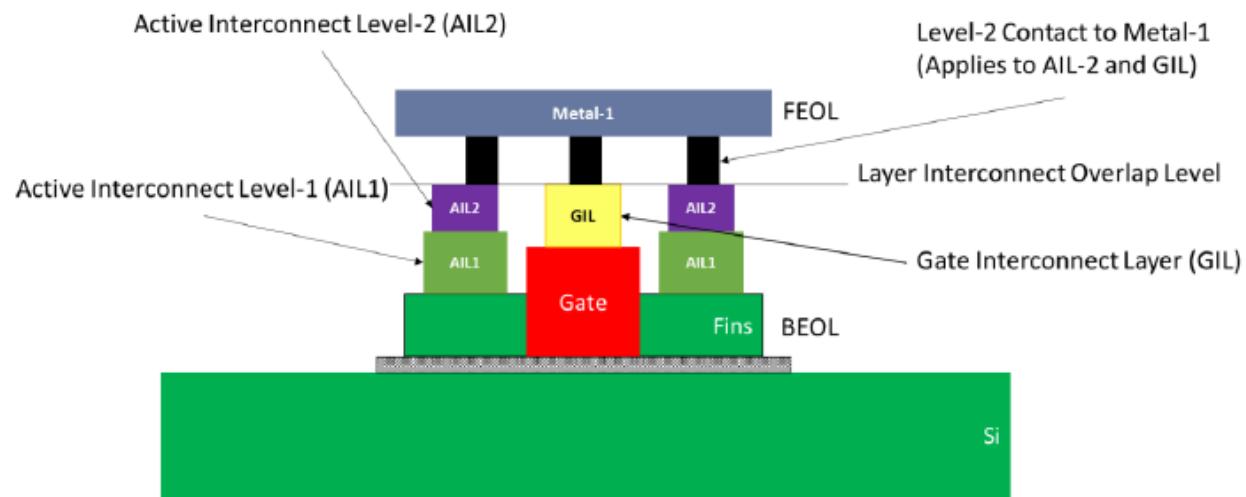
Flow of Study Project

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# Open Cell Library

- Based on FinFET FreePDK 15nm technology
- Package of standard cells
  - Includes OR, AND, inverter etc at different drive strengths
- Information of cell available
  - GDSII files
  - SPICE netlist
- Most used library in universities and research institutions
  - Independent EDA flow testing
  - Development of cell-based design flows

# FinFET Technology



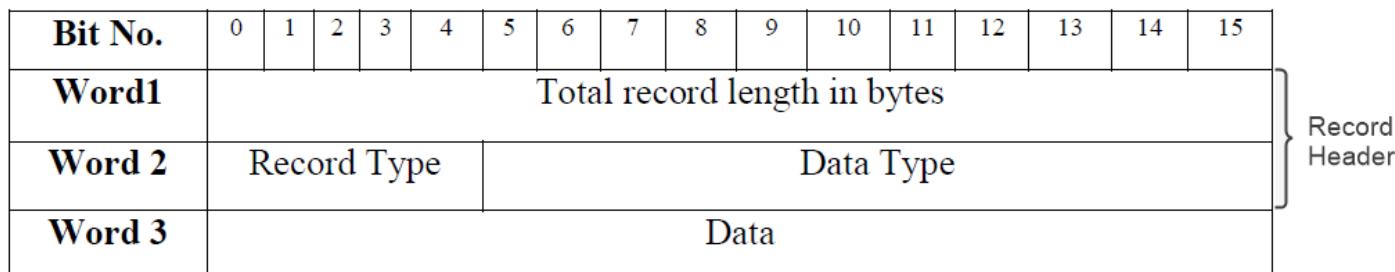
Cross-section of FinFET

# GDS/GDSII Files

- In OCL, information about the layout of the cell/circuits
- GDS/GDSII files
  - Platform independent
  - Text labels, planar geometric shapes in hierachial form
  - Binary format - difficult to read

# Record

- Sequential list of variable length records
- Record - record type, data type, data

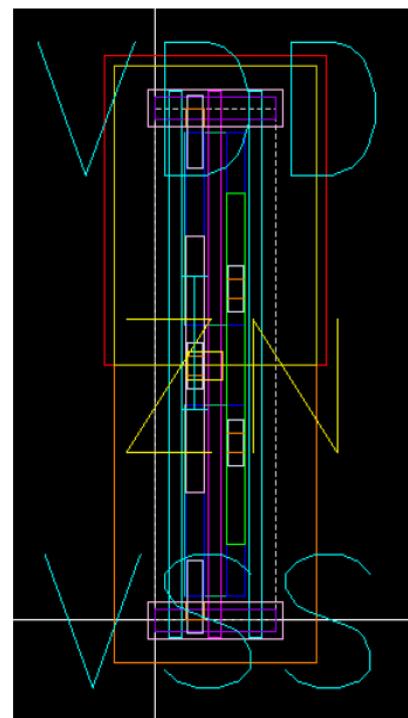


Record Fields

- 57 different record types
  - Libname, Boundary, Layer ...
- 7 different data types
  - INT2, INT4, ASCII ...

# Example: Inverter Cell

Cadence Virtuoso Tool



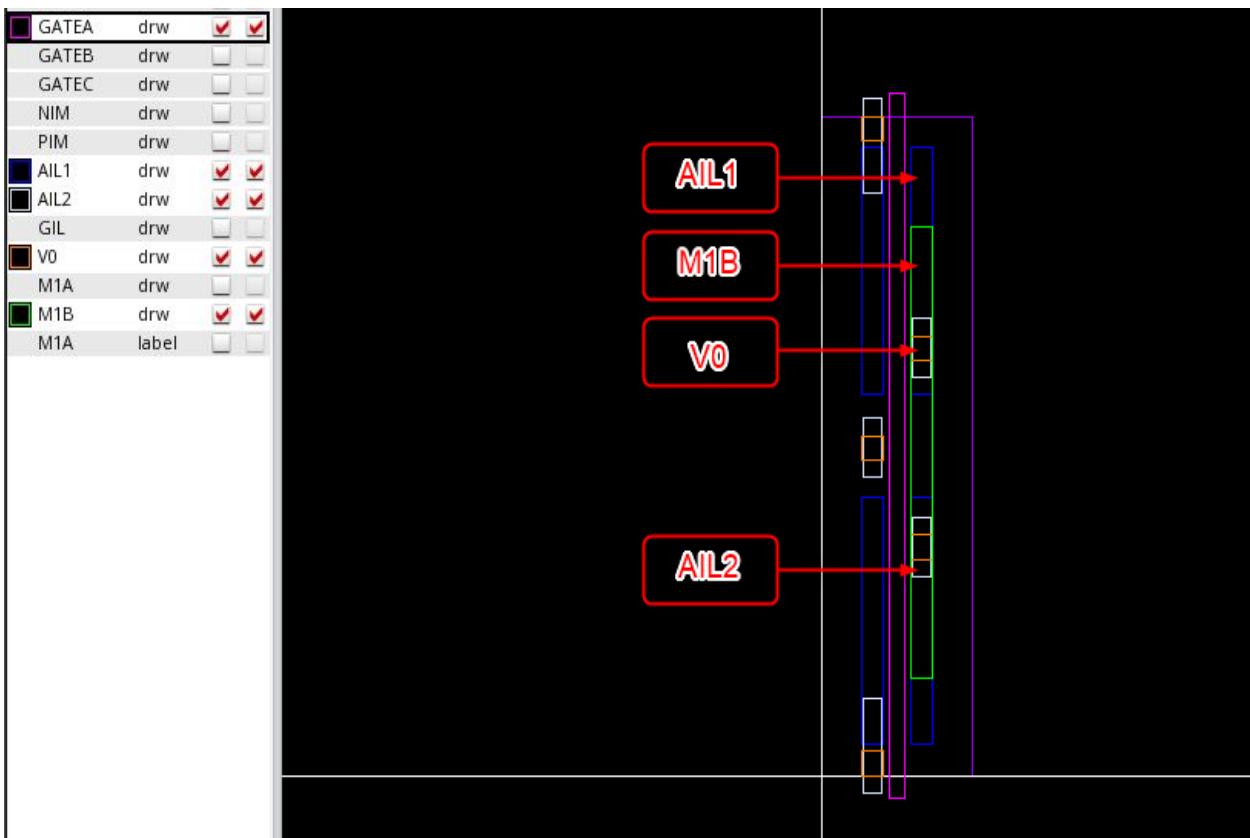
Layout of Inverter

# Layer Information

<b>Layer Name</b>	<b>Layer No.</b>
NW	0
ACT	1
GATEA	7
GATEB	8
GATEC	9
NIM	5
PIM	6

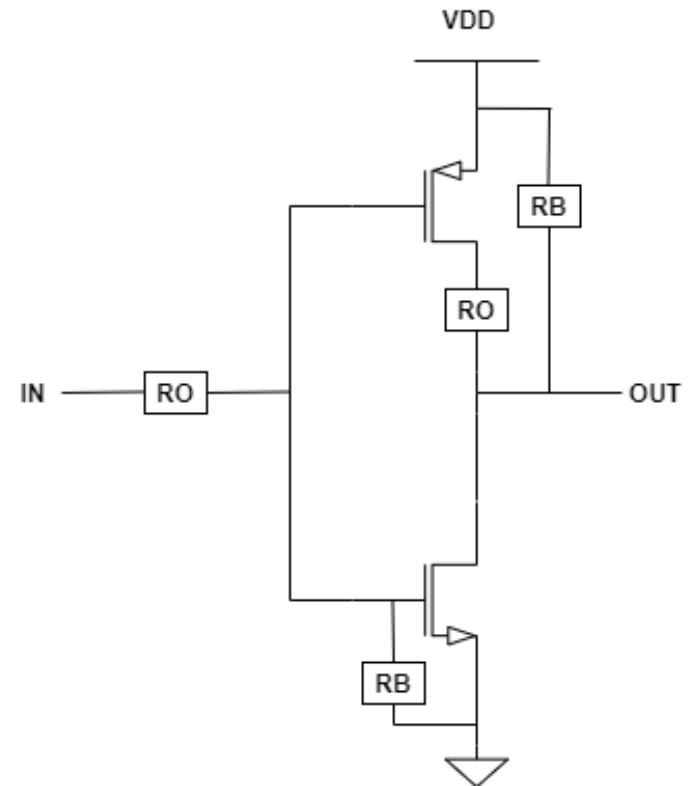
<b>Layer Name</b>	<b>Layer No.</b>
AIL1	11
AIL2	12
GIL	13
V0	14
M1A	15
M1B	16
prBoundary	200

# Interconnect Layers - GDS File



# Small Delay Defects

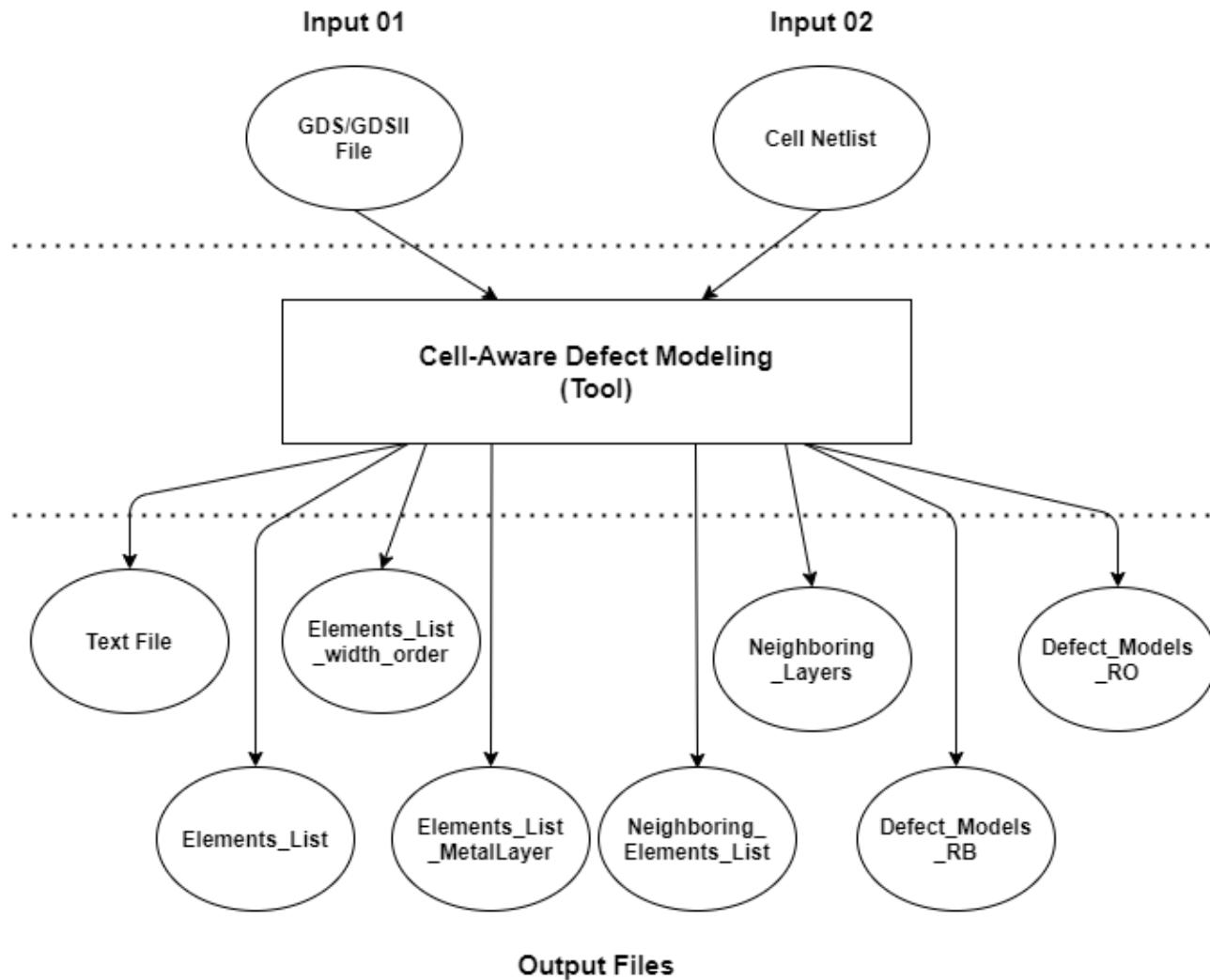
- Small delay defects - small extra delay
- Resistive defects
  - Resistive bridge
    - Examples: shorts between gates and source, neighboring wires
  - Resistive open
    - Examples: open on gate, thin wires



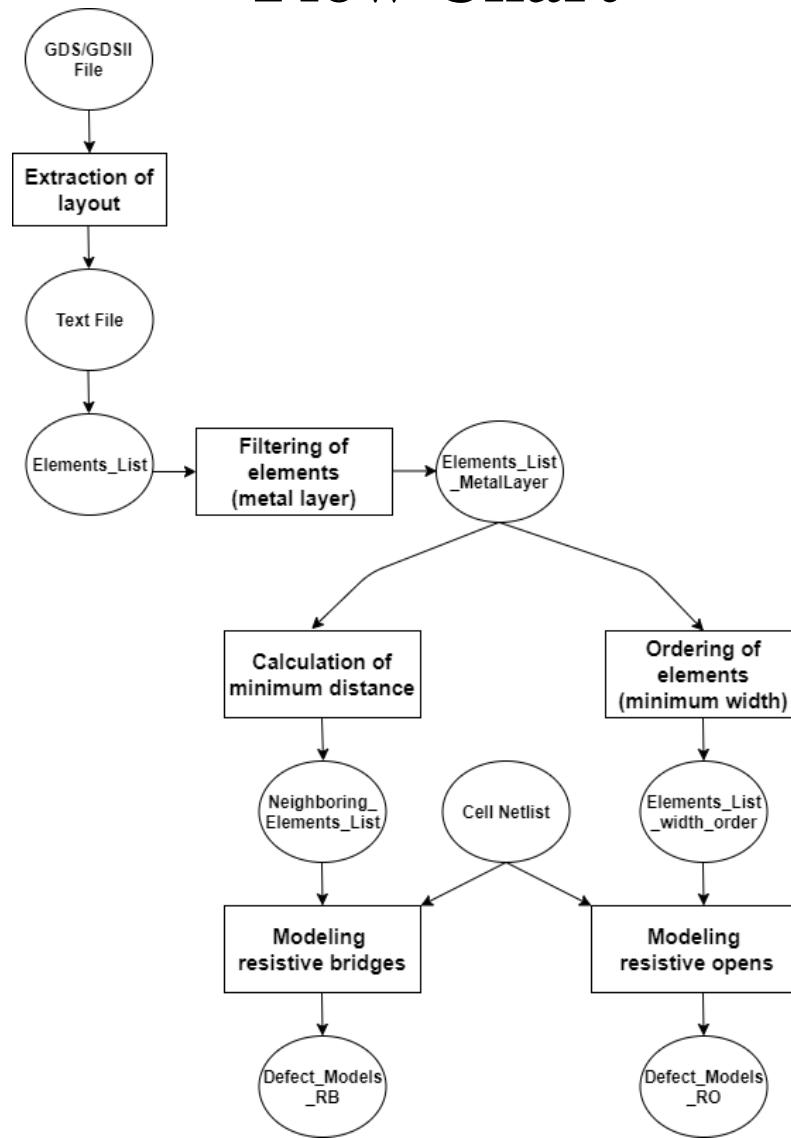
Resistive Bridge / Open : Inverter

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# Tool Overview



# Flow Chart

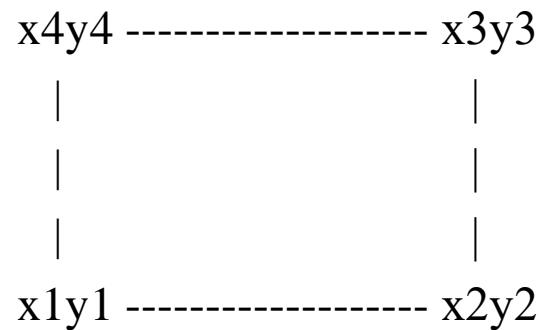


# Layout Information Extraction

- GDS/GDSII file → text file
- Python gdsii library
  - Create, read, modify, save gds files
- Based on datatypes - records can be differentiated
- Initial information: name of standard cell, library etc
- Useful information: boundary and text elements in different layers

# Boundary Element

- Boundary element - particular layer, rectangular shape  
Properties (records) :
- Layer: number
- XY: position
- XY = (x1y1, x2y2, x3y3, x4y4, x5y5)



- ENDEL: element finished with ENDEL

# Boundary Element

## TEXT FILE

RecordType: BOUNDARY

DataType: NODATA

Data: None

RecordType: LAYER

DataType: INT2

Data: (0,)

LayerNumber: 0

Layer Name: NW

RecordType: XY

DataType: INT4

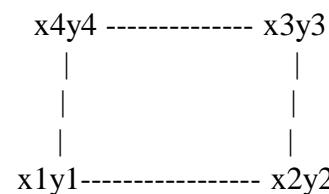
Data: (-80, 384, 272, 384, 272, 848, -80, 848, -80, 384)

Minimum Value: 352.0nm

RecordType: ENDEL

DataType: NODATA

Data: None



## CADENCE TOOL



# Text Element

- Text element - text/string displayed
  - Properties (records):
- LAYER: number the text is found
- XY: position of the text
- STRING: text to be displayed
- ENDEL: element finished with ENDEL

# Text Element

## TEXT FILE

RecordType:TEXT  
DataType:NODATA  
Data:None

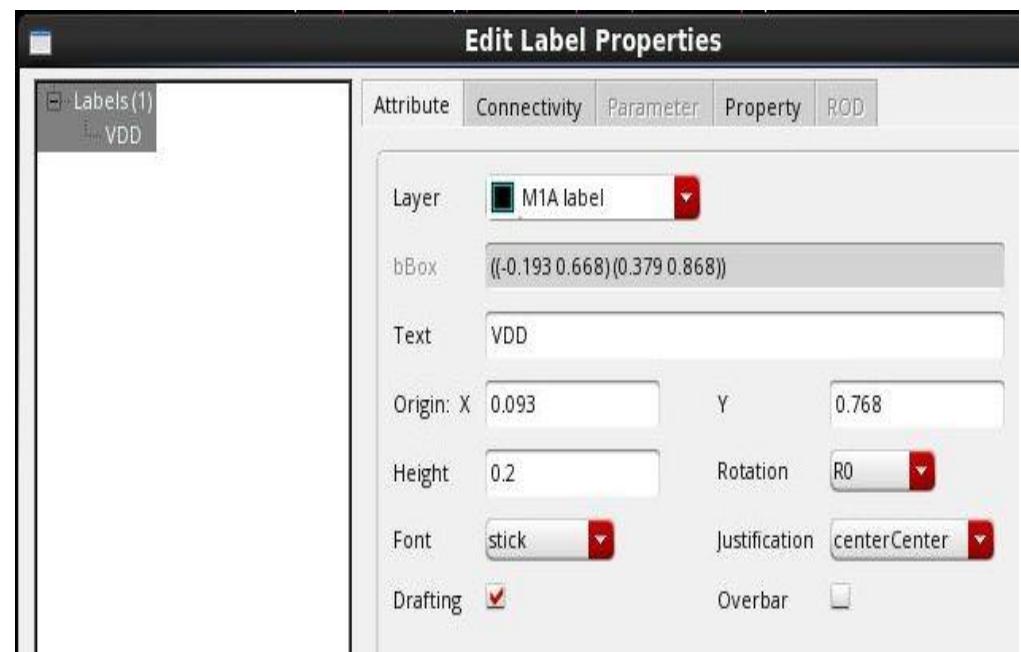
RecordType:LAYER  
DataType:INT2  
Data:(15,)  
LayerNumber:15  
Layer Name: M1A

RecordType:XY  
DataType:INT4  
Data:(93, 768)

RecordType:STRING  
DataType:ASCII  
Data:VDD

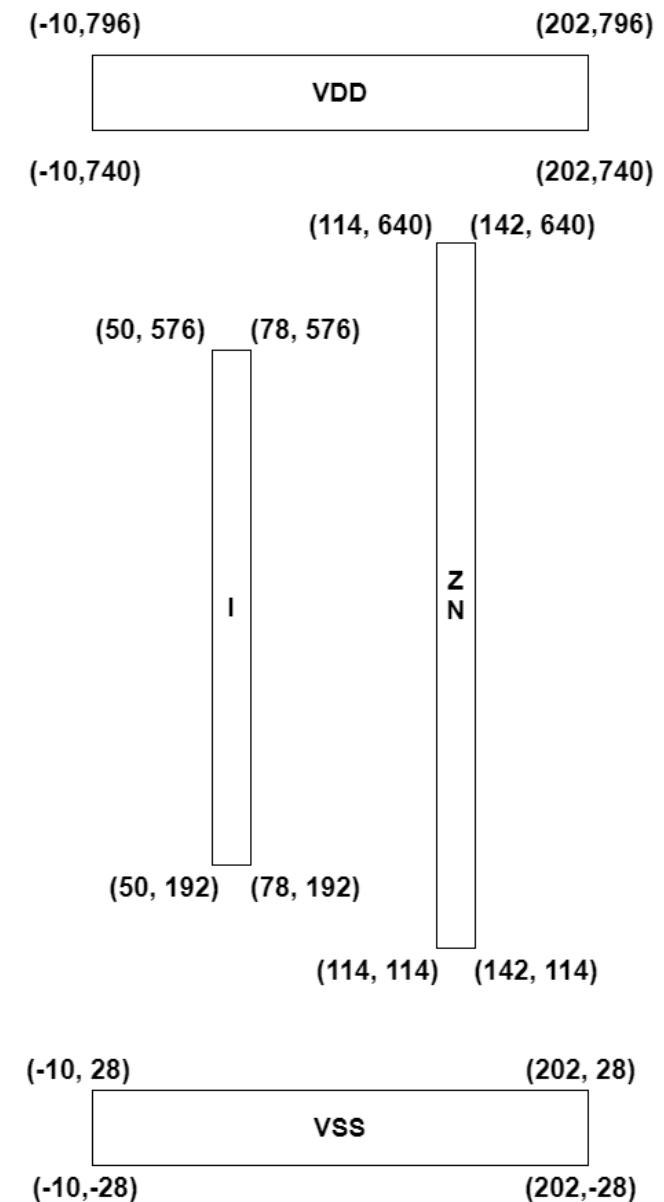
RecordType:ENDEL  
DataType:NODATA  
Data:None

## CADENCE TOOL



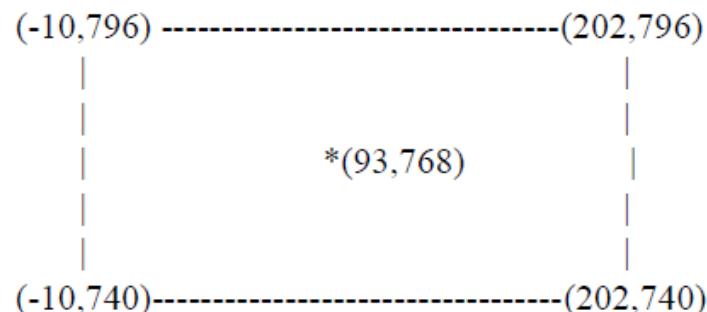
# Minimum Width

- Example:  
Minimum width [VDD]  
 $\text{minimum}(796 - 740, 202 - (-10)) = 56$



# Element List Metal Layer

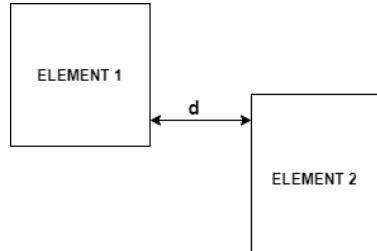
- Resistive bridge and resistive open - elements (metal layer)
- Element list - M1A: 15: 56.0: [ '-10', '-28', '202', '-28', '202', '28', '-10', '28', '-10', '-28' ]
- Mapping between boundary and text element.  
Example:



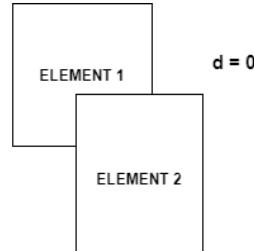
Boundary element: (-10, 740, 202, 740, 202, 796, -10, 796, -10, 740)

Text element: (93, 768), STRING: VDD

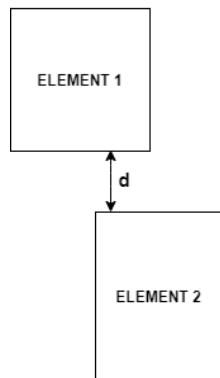
# Minimum Distance



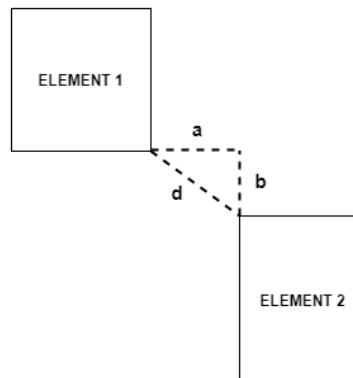
Case 01



Case 02



Case 03



Case 04

- Case 1 & 3: Minimum distance =  $d$
- Case 2: Minimum distance =  $d = 0$
- Case 4: Minimum distance =  $d = \sqrt{a^2 + b^2}$

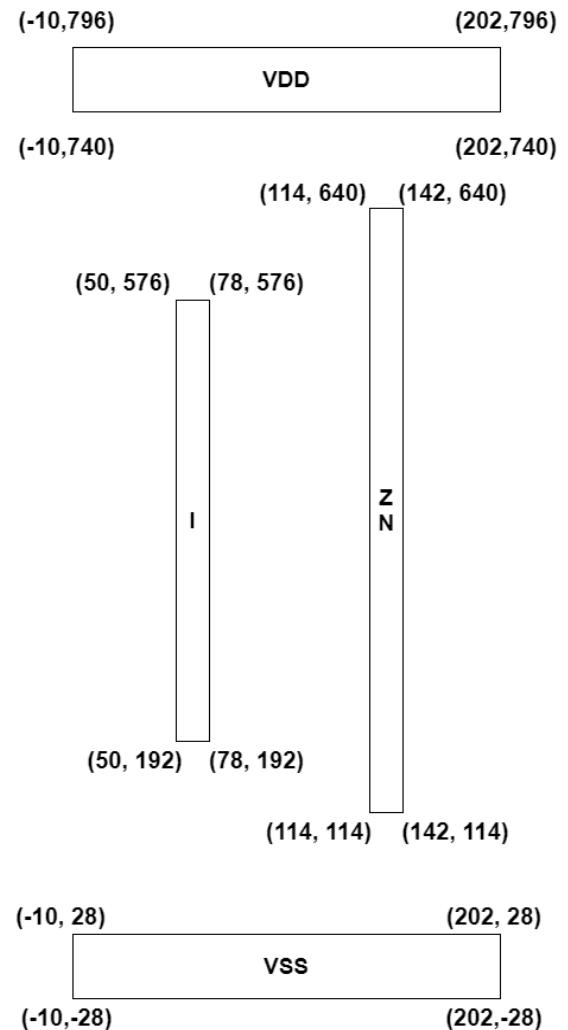
# Neighboring Elements List

- Contains information - distance between elements and the closest element to each element

- Example:

For the input (I) of an Inverter:

- I and ZN is 36.0 nm
- I and VSS is 164.0 nm
- I and VDD is 164.0 nm
- Closest Element to I-ZN



## Defect Models Generation

- Resistive bridge → neighboring elements & netlist - closest element
- Resistive open → minimum width & netlist - user input
- Default resistance “x0 = 1000” in .SUBCKT line - cell instantiation

# Resistive Bridge

- Inverter - 4 defect models with resistive bridge
- Example:

I - ZN

```
.SUBCKT INV_X1 I ZN VDD VNW VPW VSS x0=1000
*.PININFO I:I ZN:O VDD:P VNW:P VPW:P VSS:G
*.ORDERING_0_PUP M_i_1 VDD ZN
*.ORDERING_0_PDN M_i_0 VSS ZN
*.EQN ZN_0 =!I
M_i_0 ZN_0 I VSS VPW nfet W=0.288000U L=0.020000U nfin=7
M_i_1 ZN_0 I VDD VNW pfet W=0.288000U L=0.020000U nfin=7
RB1 I ZN_0 x0
RO1 ZN_0 ZN 50
.ENDS
```

# Resistive Open

- Inverter - 2 defect models with resistive open , user input - 40 nm
- Example:  
I - 28 nm

```
.SUBCKT INV_X1 I ZN VDD VNW VPW VSS x0=1000
*.PININFO I:I ZN:O VDD:P VNW:P VPW:P VSS:G
*.ORDERING_0_PUP M_i_1 VDD ZN
*.ORDERING_0_PDN M_i_0 VSS ZN
*.EQN ZN!=I
M_i_0 ZN I VSS VPW nfet W=0.288000U L=0.020000U nfin=7
M_i_1 ZN I VDD VNW pfet W=0.288000U L=0.020000U nfin=7
R01 I N1 x0
.ENDS
```

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# Summary

- Small delay defects increases at field level → results in early life failure
  - One of the sources : physical defects like resistive bridge, resistive open
- Demand for higher quality tests
- Cell-Aware Test
  - Testing the cell using the layout information
- Tool developed - to generate efficient & realistic defect models with resistive bridge & resistive open

# Future Work

- Analysis of small delays
- Running transient analysis
  - Cell instantiation with defect models
  - Different resistance values

# THANK YOU